ABSTRACT

Disclosed is a semiconductor laser device in which a ridge is formed to have a buried structure inside cleaved surfaces in order to prevent grains from being formed at the cleaved surfaces. A method for manufacturing the semiconductor laser device is also disclosed. The semiconductor laser device comprises a first-conductivity type substrate, a first-conductivity type clad layer formed over the substrate, an active layer formed over the first-conductivity type clad layer, a second-conductivity type clad layer formed over the active layer while having a ridge spaced apart, at respective opposite longitudinal ends thereof, from a laser emitting end surface and an end surface opposite to the laser emitting end surface by a predetermined gap and a current blocking layer formed on the second-conductivity type clad layer around the ridge. In accordance with the invention, it is possible to prevent formation of grains at the cleaved surfaces.